DIM1000NSM33-TS000

Single Switch IGBT Module

Replaces DS6093-3

DS6093-4 February 2022 (LN41514)

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- High Current Density Enhanced DMOS SPT
- Isolated AlSiC Base with AlN Substrates

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives
- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM1000NSM33-TS000 is a single switch 3300V, soft punch through n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

KEY PARAMETERS

V_{CES}		**3300V**
$V_{CE(sat)}$ *	(typ)	**2.2V**
I_C	(max)	**1000A**
$I_{C(PK)}$	(max)	**2000A**

* Measured at the auxiliary terminals

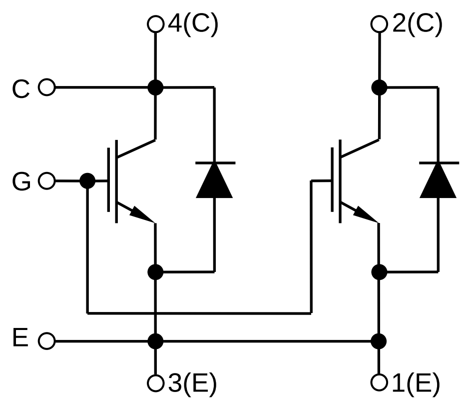


Fig. 1 Circuit configuration

Outline type code: N

(See Fig. 11 for further information)

Fig. 2 Package

ORDERING INFORMATION

Order As:

DIM1000NSM33-TS000

Note: When ordering, please use the complete part number

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	V_{GE} = 0V	3300	V
V_{GES}	Gate-emitter voltage		±20	V
I_C	Continuous collector current	T_{case} = 110°C	1000	A
$I_{C(PK)}$	Peak collector current	1ms, T_{case} = 140°C	2000	A
P_{max}	Max. transistor power dissipation	T_{case} = 25°C, T_j = 150°C	10.4	kW
I^2t	Diode I^2t value	V_R = 0, t_p = 10ms, T_j = 125°C	320	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q_{PD}	Partial discharge – per module	IEC1287, V_1 = 3500V, V_2 = 2600V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation – junction to case	-	-	12	°C/kW
$R_{th(j-c)}$	Thermal resistance – diode	Continuous dissipation – junction to case	-	-	24	°C/kW
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	°C/kW
T_j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	150	°C
T_{stg}	Storage temperature range	-	-40	-	125	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	V_{GE} = 0V, V_{CE} = V_{CES}			4	mA
		V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125°C			60	mA
		V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 150°C			100	mA
I_{GES}	Gate leakage current	V_{GE} = ± 20V, V_{CE} = 0V			1	μA
$V_{GE(TH)}$	Gate threshold voltage	I_C = 80mA, V_{GE} = V_{CE}		5.7		V
$V_{CE(sat)}$ †	Collector-emitter saturation voltage	V_{GE} = 15V, I_C = 1000A		2.2		V
		V_{GE} = 15V, I_C = 1000A, T_j = 125°C		2.8		V
		V_{GE} = 15V, I_C = 1000A, T_j = 150°C		3.0		V
I_F	Diode forward current	DC		1000		A
I_{FM}	Diode maximum forward current	t_p = 1ms		2000		A
V_F †	Diode forward voltage (IGBT arm)	I_F = 1000A		2.4		V
		I_F = 1000A, T_j = 125°C		2.5		V
		I_F = 1000A, T_j = 150°C		2.4		V
C_{ies}	Input capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		170		nF
Q_g	Gate charge	±15V Including external C_{ge}		17		μC
C_{res}	Reverse transfer capacitance	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		4		nF
L_M	Module inductance			15		nH
R_{INT}	Internal resistance			135		μΩ
SC_{Data}	Short circuit current, I_{SC}	T_j = 150°C, V_{CC} = 2500V t_p ≤ 10μs, V_{GE} ≤ 15V $V_{CE\ (max)}$ = V_{CES} – L^* x dI/dt IEC 60747-9		3700		A

Note:

† Measured at the auxiliary terminals

* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 1000A V_{GE} = ±15V V_{CE} = 1800V $R_{G(ON)}$ = 2.2Ω $R_{G(OFF)}$ = 2.2Ω C_{ge} = 220nF L_S ~ 100nH		2700		ns
t_f	Fall time			520		ns
E_{OFF}	Turn-off energy loss			1950		mJ
$t_{d(on)}$	Turn-on delay time			1000		ns
t_r	Rise time			400		ns
E_{ON}	Turn-on energy loss			1300		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 1000A		567		μC
I_{rr}	Diode reverse recovery current	V_{CE} = 1800V		614		A
E_{rec}	Diode reverse recovery energy	dI_F/dt = 2700A/μs		700		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 1000A V_{GE} = ±15V V_{CE} = 1800V $R_{G(ON)}$ = 2.2Ω $R_{G(OFF)}$ = 2.2Ω C_{ge} = 220nF L_S ~ 100nH		2750		ns
t_f	Fall time			570		ns
E_{OFF}	Turn-off energy loss			2200		mJ
$t_{d(on)}$	Turn-on delay time			1020		ns
t_r	Rise time			420		ns
E_{ON}	Turn-on energy loss			1700		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 1000A		1050		μC
I_{rr}	Diode reverse recovery current	V_{CE} = 1800V		870		A
E_{rec}	Diode reverse recovery energy	dI_F/dt = 2700A/μs		1250		mJ

T_{case} = 150°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(off)}$	Turn-off delay time	I_C = 1000A V_{GE} = ±15V V_{CE} = 1800V $R_{G(ON)}$ = 2.2Ω $R_{G(OFF)}$ = 2.2Ω C_{ge} = 220nF L_S ~ 100nH		2800		ns
t_f	Fall time			550		ns
E_{OFF}	Turn-off energy loss			2300		mJ
$t_{d(on)}$	Turn-on delay time			1030		ns
t_r	Rise time			430		ns
E_{ON}	Turn-on energy loss			1850		mJ
Q_{rr}	Diode reverse recovery charge	I_F = 1000A		1100		μC
I_{rr}	Diode reverse recovery current	V_{CE} = 1800V		800		A
E_{rec}	Diode reverse recovery energy	dI_F/dt = 2700A/μs		1300		mJ

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

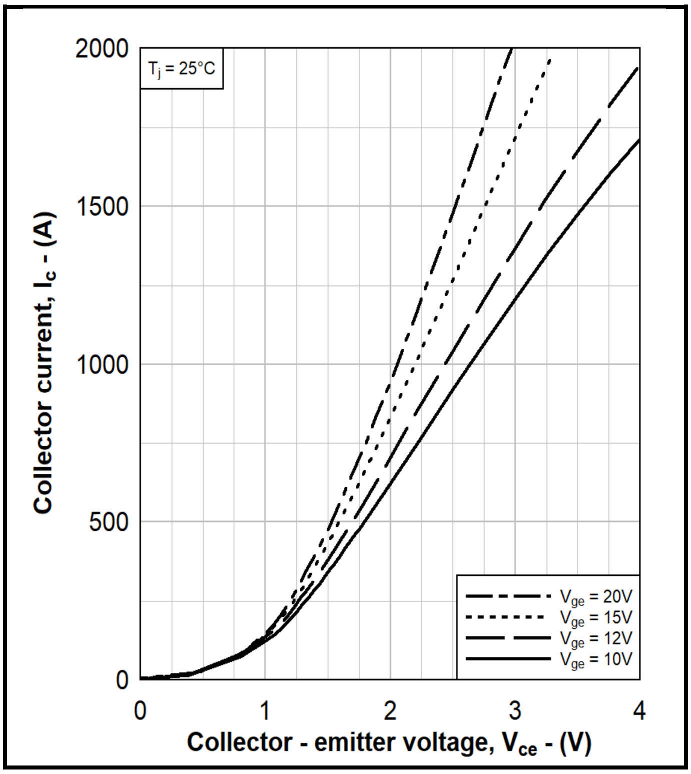


Fig. 3 Typical output characteristics

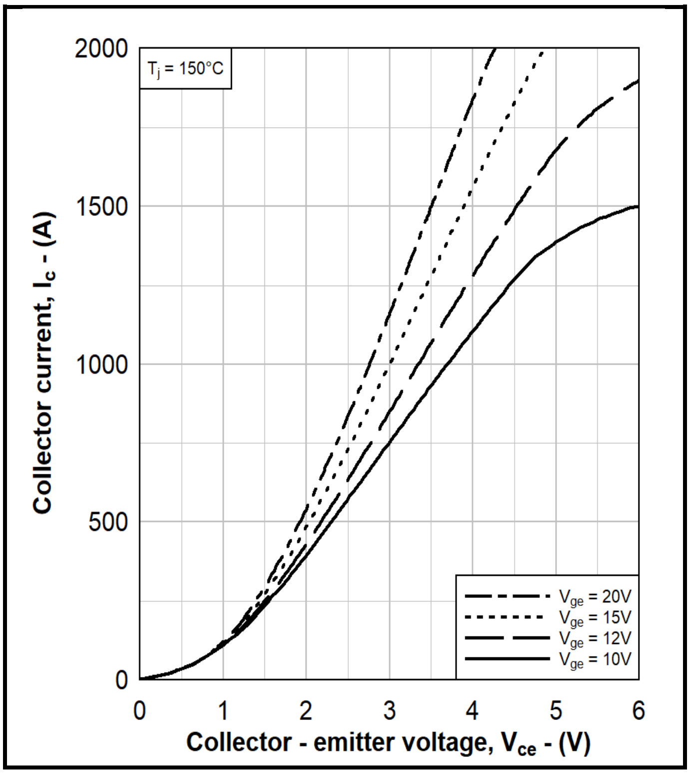


Fig. 4 Typical output characteristics

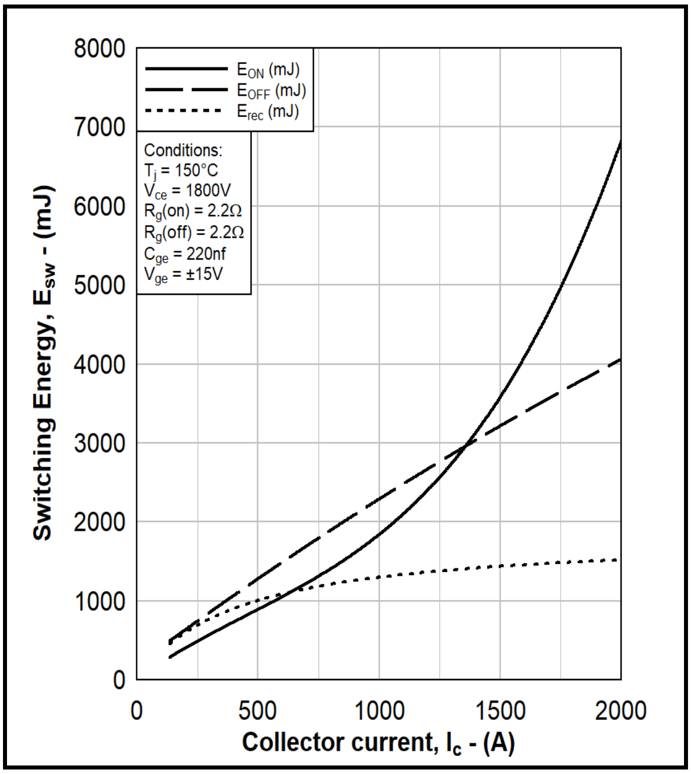


Fig. 5 Typical switching energy vs collector current

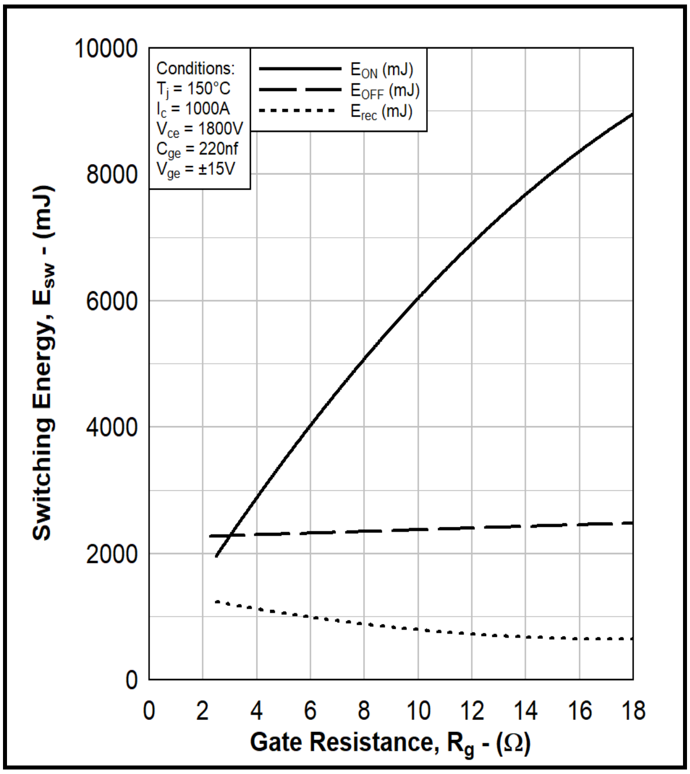


Fig. 6 Typical switching energy vs gate resistance

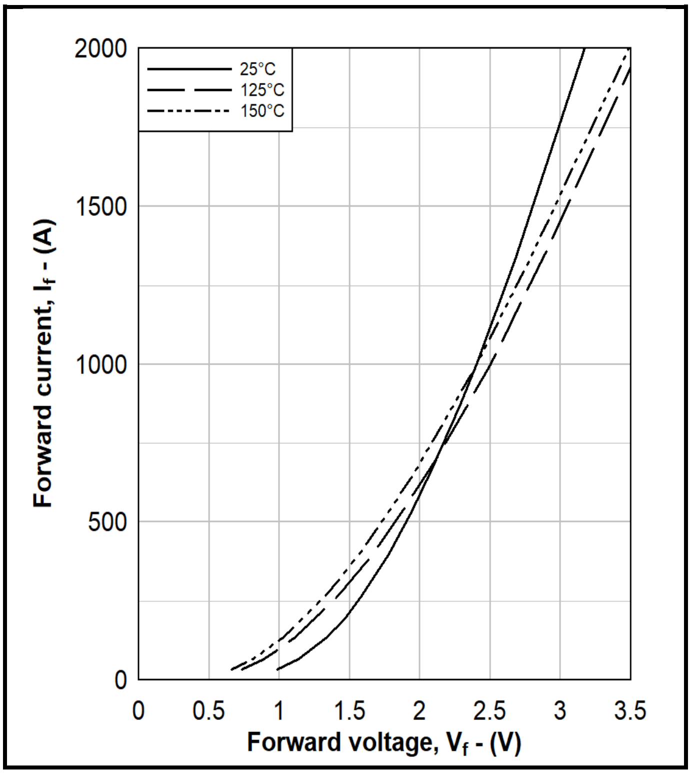


Fig. 7 Diode typical forward characteristics

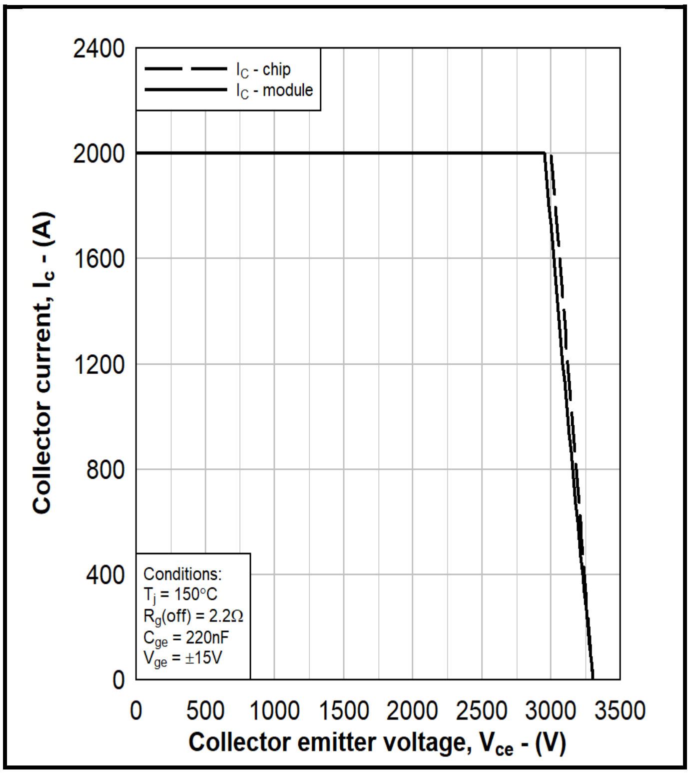


Fig. 8 Reverse bias safe operating area

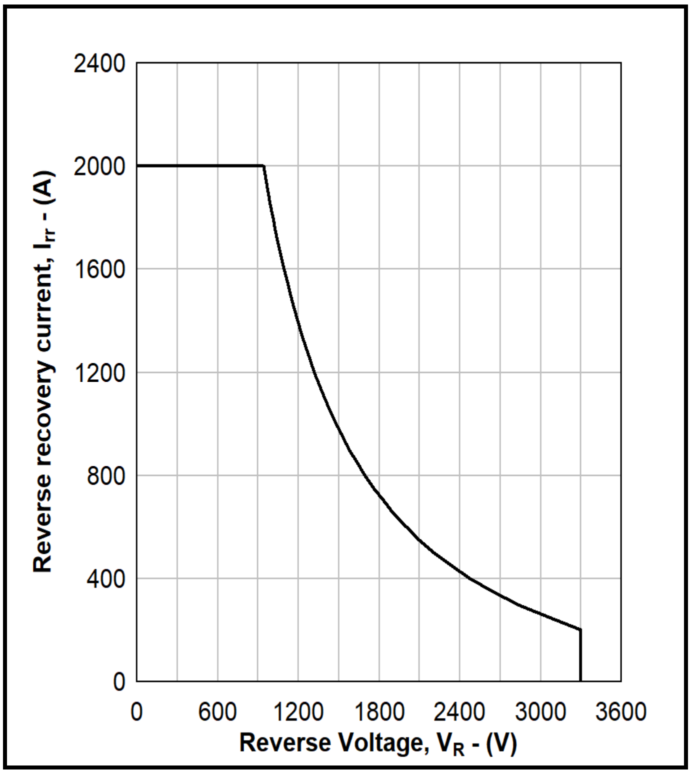


Fig. 9 Diode reverse bias safe operating area

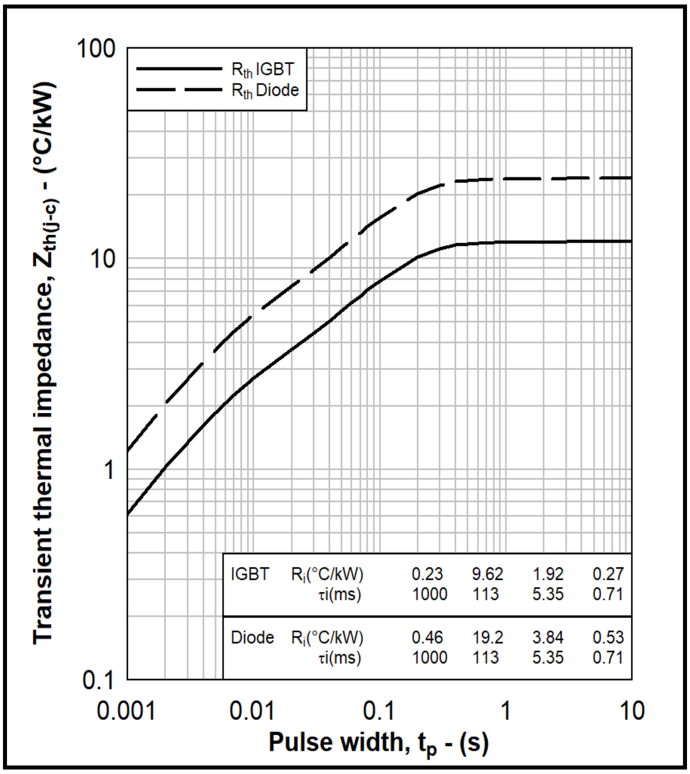
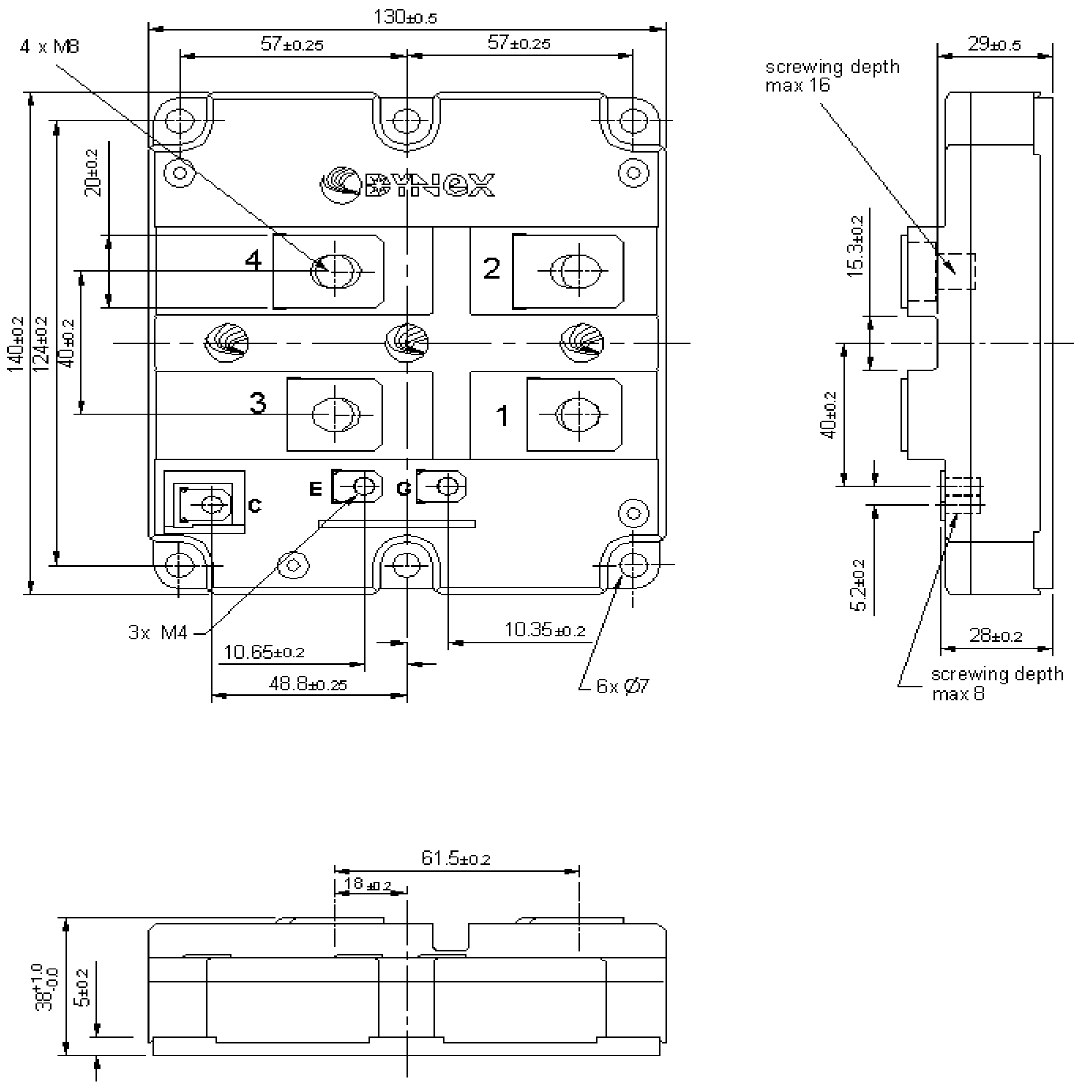


Fig. 10 Transient thermal impedance

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



Nominal Weight: 900g

Module Outline Type Code: N

Fig. 11 Module outline drawing

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